

# 9

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## The Normal Colpitts Oscillator

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### 9.1 INTRODUCTION

This chapter develops the additional and/or modified relations of Chapters 5 and 7 required to design this type of oscillator. It also contains comments about the practical aspects of the design. Finally, it formulates two design algorithms—one for each of the major types of limiting of Section 6.2. The algorithms are specifically applicable to the self-limiting types of crystal oscillator but they are also useful for non-self-limiting types and for other types of two-terminal resonators.

By the normal Colpitts oscillator is meant the oscillator whose circuit is shown in Fig. 5.1*b* and repeated in a modified form in Fig. 5.8. All the components in that figure are physical; that is, they are all installed components.

The theory of the oscillator is fully covered in Chapter 5, except for the limiting considerations. It is therefore recommended that Chapter 5 be read in its entirety, beginning with Section 5.3.4, before proceeding with this chapter.

Many of the equations developed in Chapter 7 for the Pierce oscillator will also be used for formulating the design algorithms and will be referenced therein in the “Text Equation” column. In using these equations,  $V_{be}$  or  $V_{be'}$ , as appropriate, must be substituted for  $V_b$  in the equations of Chapter 7.

### 9.2.1 Introduction

### 9.2.2 Discussion of $V_{L_{\max}}$ and $R_L$

### 9.2.2.1 Calculation of $V_{L_{\max}}$ for the Collector Base Limiting Oscillator

Figure 9.1 shows the voltage relationships in this type of limiting. By inspection it is seen to be

(9.1)

$$v_{CE_{\max}} \leq BV_{CE} \quad (9.2)$$


Figure 9.1 Voltage relationships for collector base voltage limiting in the Colpitts oscillator.

therefore,

$$\begin{aligned}
 V_L &\leq \frac{BV_{CE} - 1.4V_{be'}}{2.8} \\
 &\leq 0.357BV_{CE} - 0.5V_{be'} \\
 &\approx 0.33BV_{CE}
 \end{aligned} \tag{9.3}$$

to compensate for the  $V_{be'}$  term.

#### 9.2.2.2 Calculation of $V_{L_{max}}$ for the $be$ Cutoff Limiting Oscillator

Figure 9.2 shows the voltage relationship for this type of limiting. In this oscillator  $v_{B_{max}}$  must be less than  $v_C = V_{BB}$  for  $Z_3$  having the minimum  $R_3$ . Since the oscillator is designed for  $R_{3_{max}}$ , when  $V_L$  is minimum, provision must be made for the increase of  $V_L$  as  $R_3$  decreases. Let

$$\frac{R_{3_{max}}}{R_{3_{min}}} = 2 \tag{9.4}$$

then

$$\frac{V_{L_{max}}}{V_{L_{min}}} \approx 1.5 \tag{9.5}$$

and from Eq. (9.3)

$$V_L = \frac{0.33}{1.5}BV_{CE} = 0.22BV_{CE} \tag{9.6}$$

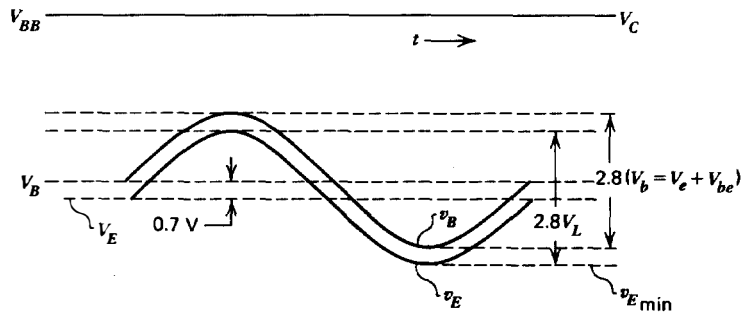


Figure 9.2 Voltage relationships for the base emitter cutoff limiting in the Colpitts oscillator.

### 9.2.2.3 Calculation of $V_E$ , Which Should Be Greater Than 2 V

It is evident from Fig. 9.1 that, for collector limiting,

$$\begin{aligned} V_E &= V_{BB} - [1.4(V_L + V_{be'}) - 700] - 700 \\ &= V_{BB} - 1.4(V_L + V_{be'}) \end{aligned} \quad (9.7)$$

Similarly, from Fig. 9.2, for the  $be$  cutoff limiting oscillator

$$V_E = V_{BB} - 2.1(V_L + V_{be}) - 1700 \quad (9.8)$$

or, when

$$V_{E1} > \frac{V_{BB}}{2}, \quad V_E = \frac{V_{BB}}{2} \quad (9.8a)$$

which is derived in the same manner as that described in Section 7.2.4.3.2, to which the reader is referred.

### 9.2.3 Calculation of $C_{r2}$

It is desirable that

$$X_{C_{r2}} \leq 0.02 X_{L_N} \quad (9.9)$$

in order not to affect the stability of  $X_{L_N}$  and

$$C_{r2} = \frac{159,000}{X_{C_{r2}} f} \quad (9.10)$$

## 9.3 FREQUENCY VARIATIONS DUE TO EXTERNAL FACTORS

The material in Section 7.3 is completely applicable.

## 9.4 THE DESIGN PROCEDURE

The design procedure outlined in Section 7.4 is applicable except that there are two levels of approximation. It is therefore seen that the design for the Colpitts oscillator is more difficult than that for the Pierce oscillator.

## 9.5 THE COLPITTS OSCILLATOR, COLLECTOR BASE LIMITING

### 9.5.1 The Design Algorithm for This Oscillator (Algorithm 12.4)

See Section 7.5.1 for pertinent remarks which are also applicable to this algorithm.

It will be noted that Steps 6 to 20 constitute the first level of approximation, and Steps 22 to 28, the second level. The remaining steps constitute the translation of the calculated quantities into the physical components which make up the oscillator.

### 9.5.2 Design Examples for Algorithm 12.4

Design Examples 9.1 and 9.2 are design examples for this algorithm. The results are quite similar to those for the design examples for Algorithm 12.1 discussed in Section 7.5.2. The major differences are that  $I_{BB}$  is larger because of the greater losses, and the operating  $Q$  is somewhat smaller.

### 9.5.3 Trimming for Algorithm 12.4

See Fig. 5.8.

#### 9.5.3.1 Introduction

See Section 7.5.3.1.

#### 9.5.3.2 Basis of the Trimming Procedure

The trimming is based upon the following approximate relations:

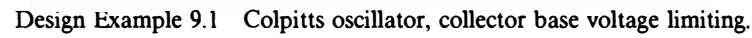
$$\begin{array}{ll} 1 & V_L \propto V_{CE} \\ & \text{from Eq. (9.3).} \end{array} \quad (9.11)$$

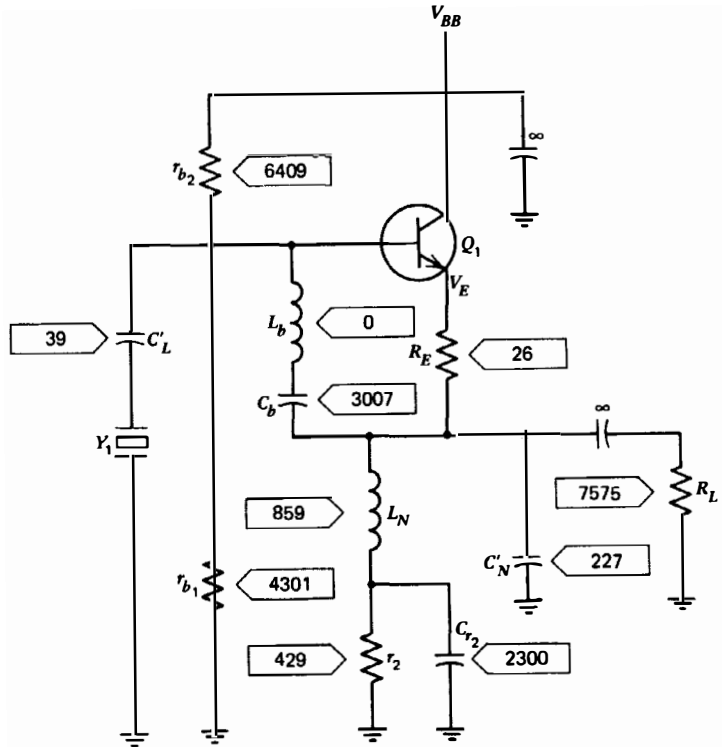
$$\begin{array}{ll} 2 & |I_3| \approx \frac{V_L}{\sqrt{R_3^2 + X_2^2}} \\ & \text{from Eq. (5.65).} \end{array} \quad (9.12)$$

$$\begin{array}{ll} 3 & V_{be} \approx |I_3| |X_1| \\ & \text{from Eq. (5.52a).} \end{array} \quad (9.13)$$

$$\begin{array}{ll} 4 & P_L \propto \frac{V_L^2}{R_L} \end{array} \quad (9.14)$$

5  $|V_{be}|$  and  $I_E$  must be maintained so that the proper type of limiting is in effect. This is a rather broad requirement and will permit large ranges of  $|V_{be}|$  and  $I_E$ , the values of which must be optimized for lowest  $X_1$  and

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Design Example 9.2 Colpitts oscillator, collector base voltage limiting.

All units in				
$\varnothing$	MHz	$\varnothing$	mW	pF
mA, mV dc or rms				
Oscillator Performance	Item	Value		
	$f$	0.8		
	$P_L$	3.3		
	$P_x$	10		
	$V_{BB}$	10.000		
Principal Crystal Data	$R_{df}$	625		
	$I_x$	4		
	Cut	AT		
	$N$	1		
Transistor Data	$\beta_o$	30		
	$f_T$	700		
	$BV_{CE}$	15000		
	$C_{cb}$	1		
	$C_{bet}$	2		
	$C_{ce}$	2		
	$P_{dis}$			
	Type	2N918		
Circuit Parameters	$A_{i,0}$	2		
	$\eta$	0.33		
Calculated Data	$I_{BB}$	6.8		
	$V_E$	2633		
	$g_m$	0.016		

highest conversion efficiency, consistent with the variations in transistor properties. This may involve adjustments in the values of  $r_2$ ,  $r_{b1}$ , and  $r_{b2}$ .

*Note:* For a crystal resonator,  $I_3 \equiv I_x$ .

### 9.5.3.3 Typical Trimming Steps

Section 7.5.3.3 is applicable, taking into account the number changes of the equivalent equations.

### 9.5.4 Frequency Instability Due to Variations in Components, Other Than $Z_3$

Section 7.5.4 is applicable.

## 9.6 THE COLPITTS OSCILLATOR, *be* CUTOFF LIMITING

9.6.1 The design algorithm for the oscillator is Algorithm 12.5. The comments in Section 7.6.1 are applicable here.

### 9.6.2 Design Examples for Algorithm 12.5

Design Examples 9.3 and 9.4 pertain to Algorithm 12.5. The results are quite similar to those for the design examples for Algorithm 12.2 discussed in Section 7.6.2. The major differences are that  $I_{BB}$  is larger because of the greater losses, and the operating  $Q$  is somewhat smaller.

### 9.6.3 Trimming for Algorithm 12.5

See Fig. 5.8.

#### 9.6.3.1 Introduction

Same as Section 7.5.3.1.

#### 9.6.3.2 Basis of the Trimming Procedure

The trimming is based upon the following relations:

$$\begin{array}{ll} 1 & I_3 = 1.4I_e \end{array} \quad (9.15)$$

from Fig. 2.12*b*.

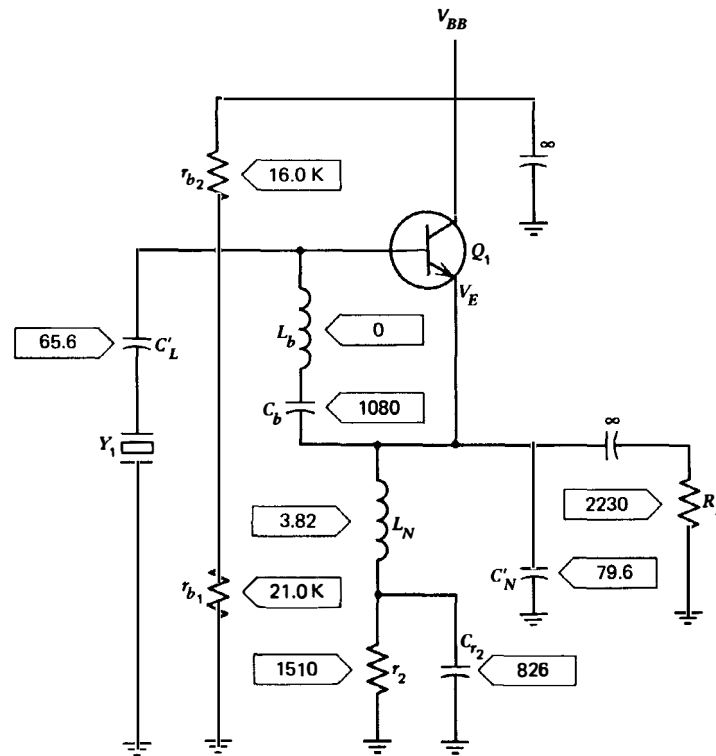
$$\begin{array}{ll} 2 & |V_L| = |I_3| \sqrt{R_T^2 + X_2^2} \end{array} \quad (9.16)$$

from Eq. (5.66).

$$= |I_e| \frac{|X_2|}{R_T} \sqrt{R_T^2 + X_2^2} \quad (9.17)$$

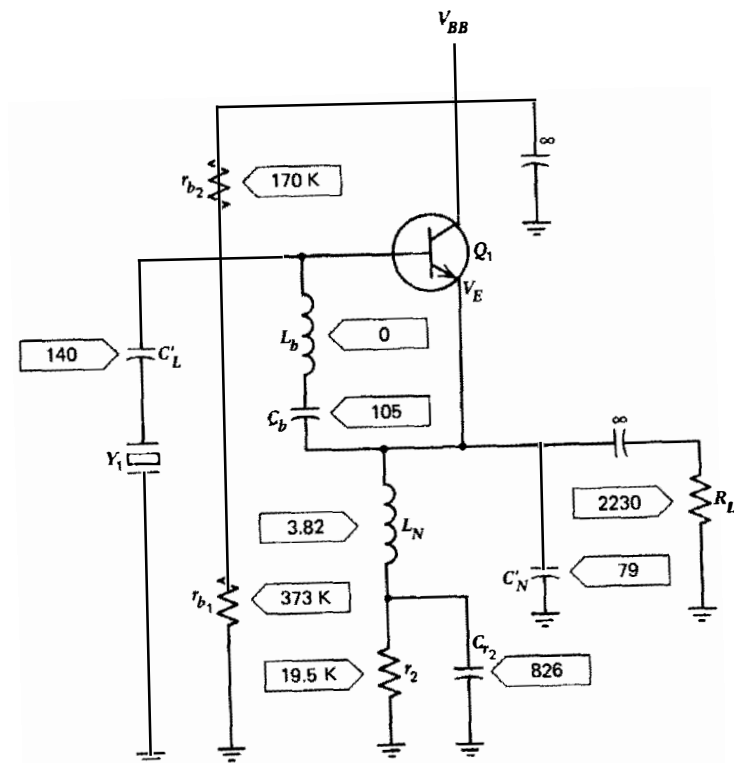
from Eq. (5.59a).





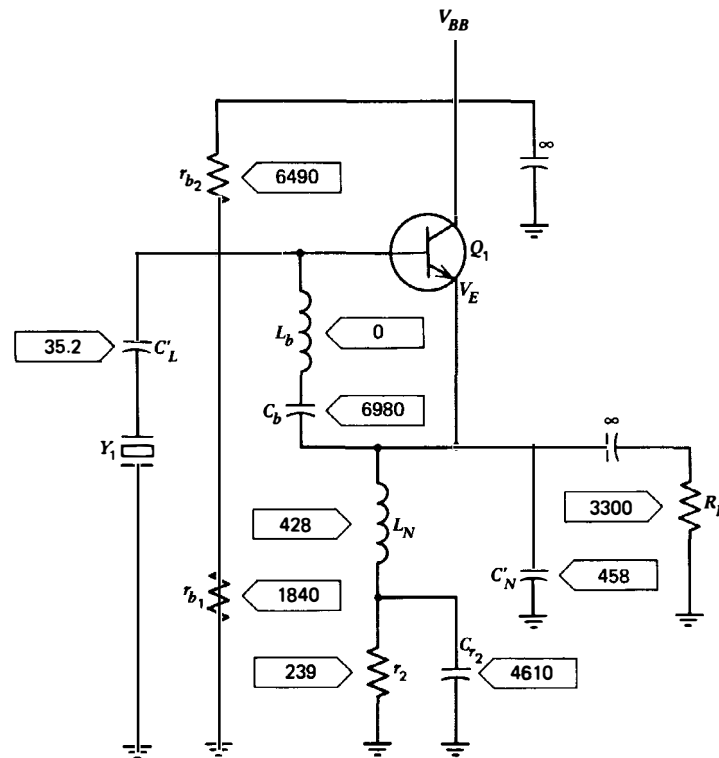
Design Example 9.3 Colpitts oscillator, base emitter cutoff limiting.

All units in		
	$\Omega$	mW
	MHz	pF
	$\mu$ A, mV dc or rms	$\mu$ H
Oscillator Performance	Item	Value
	$f$	20
	$P_L$	1.66
	$P_x$	5.0
Principal Crystal Data	$V_{BB}$	10,000
	$R_{df}$	20
	$I_x$	15.8
	Cut	AT
Transistor Data	$N$	1
	$C_L$	32
	$\beta_o$	30
	$f_T$	700
	$BV_{CE}$	15,000
	$C_{cb}$	1
	$C_{bet}$	2
	$C_{ce}$	2
	$P_{dis}$	
	Type	2N918
Circuit Parameters	$\alpha$	0.30
	$\gamma_1$	1.4
	$V_{be}$	113
	$\eta$	0.33
Calculated Data	$I_{BB}$	2.97
	$V_E$	4010
	$g_m$	0.033



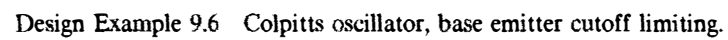
Design Example 9.4 Colpitts oscillator, base emitter cutoff limiting.

All units in				
$\Omega$	MHz	$\Omega$	mW	pF
mA, mV dc or rms				
Oscillator Performance		Item	Value	
		$f$	20	
		$P_L$	0.0166	
		$P_x$	0.05	
		$V_{BB}$	10,000	
Principal Crystal Data		$R_{df}$	20	
		$I_x$	1.58	
		Cut	AT	
		$N$	1	
Transistor Data		$\beta_o$	30	
		$f_T$	700	
		$BV_{CE}$	15,000	
		$C_{cb}$	1	
		$C_{be}$	2	
		$C_{ce}$	2	
		$P_{dis}$		
		Type	2N918	
Circuit Parameters		$\alpha$	0.3	
		$\gamma_1$	1.4	
		$V_{be}$	113	
		$\eta$	0.33	
Calculated Data		$I_{BB}$	0.28	
		$V_E$	5000	
		$g_m$	0.0032	



Design Example 9.5 Colpitts oscillator, base emitter cutoff limiting.

All units in		
$\omega$	MHz	$\Omega$
$I$	mA	mW
$V$	mV dc or rms	pF
$\mu$		$\mu$ H
Oscillator Performance	Item	Value
	$f$	0.8
	$P_L$	3.3
	$P_x$	10.0
	$V_{BB}$	10,000
Principal Crystal Data	$R_{df}$	625
	$I_x$	4.0
	Cut	AT
	$N$	1
	$C_L$	32
Transistor Data	$\beta_o$	30
	$f_T$	700
	$BV_{CE}$	15,000
	$C_{cb}$	1
	$C_{bet}$	2
	$C_{ce}$	2
	$P_{dis}$	
	Type	2N918
Circuit Parameters	$\alpha$	0.3
	$\gamma_l$	1.4
	$V_{be}$	113
	$\eta$	0.33
	$I_{BB}$	5.98
Calculated Data	$V_E$	1130
	$g_m$	0.057

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